

## RQJ0601DGDQS

Silicon P Channel MOS FET  
Power Switching

REJ03G1266-0300

Rev.3.00

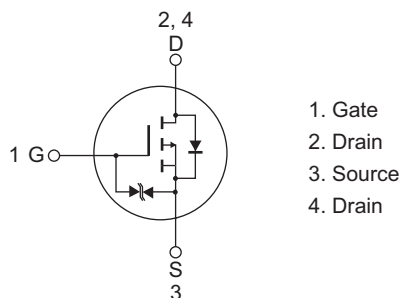
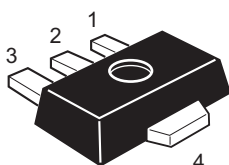
Jun 05, 2006

### Features

- Low on-resistance  
 $R_{DS(on)} = 124 \text{ m}\Omega$  typ ( $V_{GS} = -10 \text{ V}$ ,  $I_D = -1.4 \text{ A}$ )
- Low drive current
- High speed switching
- 4.5 V gate drive

### Outline

RENESAS package code: PLZZ0004CA-A  
(Package name: UPAK®)



Note: Marking is "DG".

\*UPAK is a trademark of Renesas Technology Corp.

### Absolute Maximum Ratings

( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Ratings	Unit
Drain to source voltage	$V_{DSS}$	-60	V
Gate to source voltage	$V_{GSS}$	+10 / -20	V
Drain current	$I_D$	-2.8	A
Drain peak current	$I_{D(pulse)}$ <sup>Note1</sup>	-4.2	A
Body - drain diode reverse drain current	$I_{DR}$	-2.8	A
Channel dissipation	$P_{ch}$ <sup>Note2</sup>	1.5	W
Channel dissipation	$P_{ch(pulse)}$ <sup>Note1</sup>	5	W
Channel temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$

Notes: 1.  $PW \leq 1 \text{ s}$ , duty cycle  $\leq 1\%$

2. When using the glass epoxy board (FR-4: 40 x 40 x 1 mm)

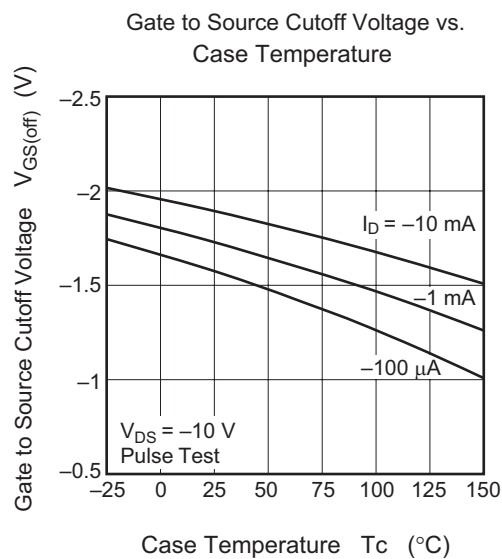
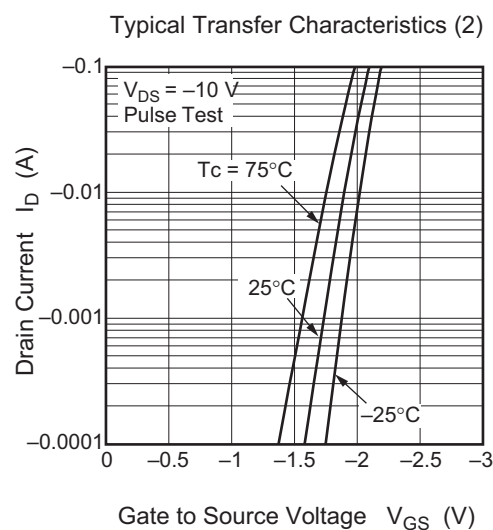
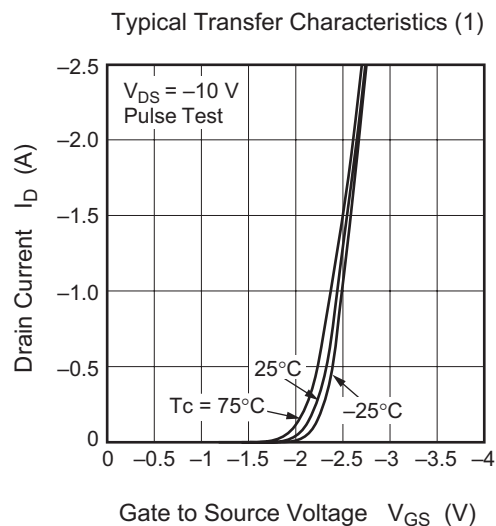
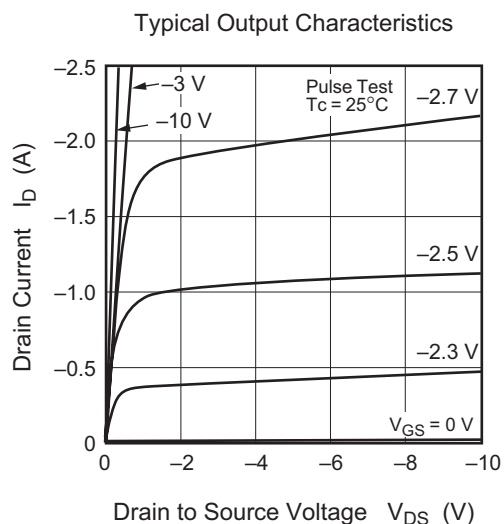
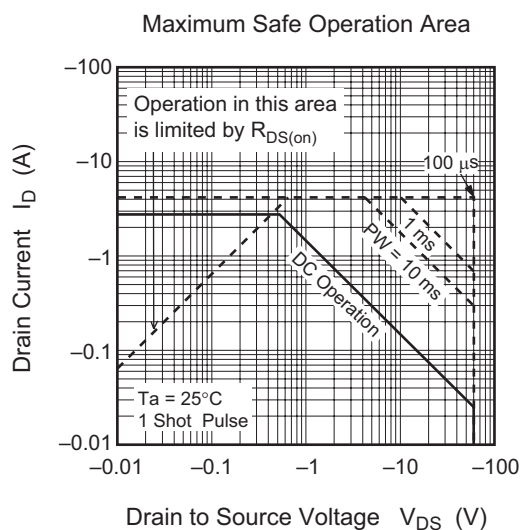
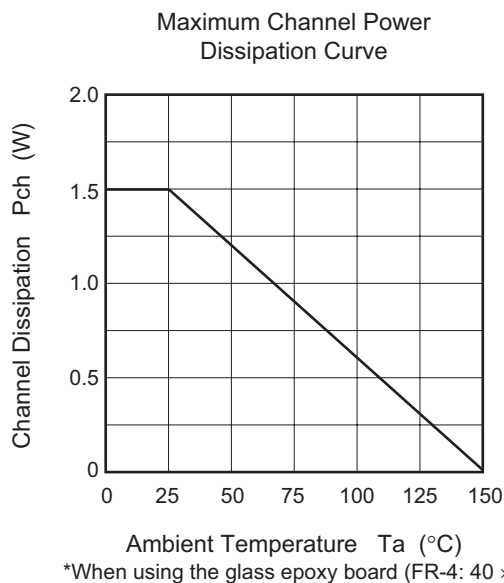
## Electrical Characteristics

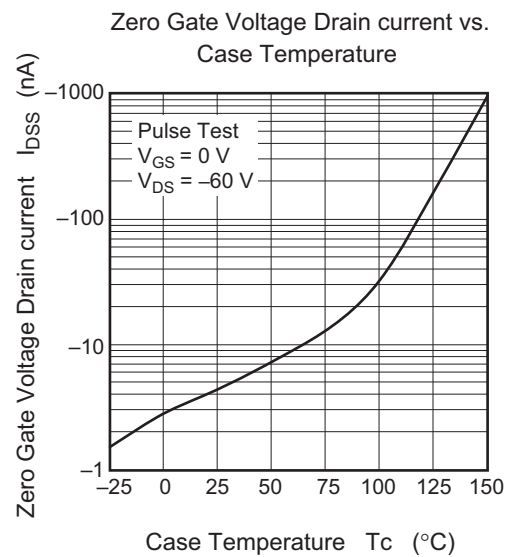
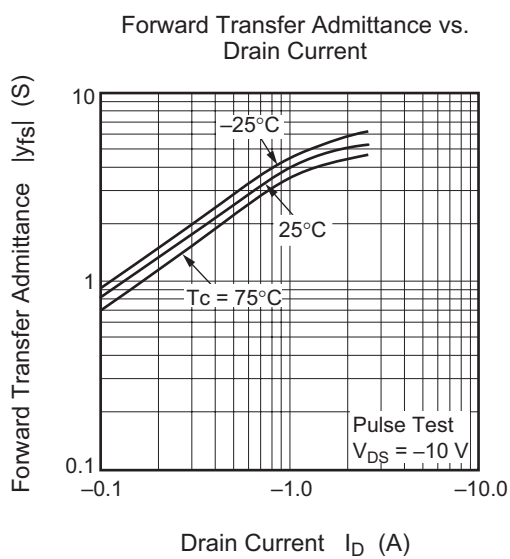
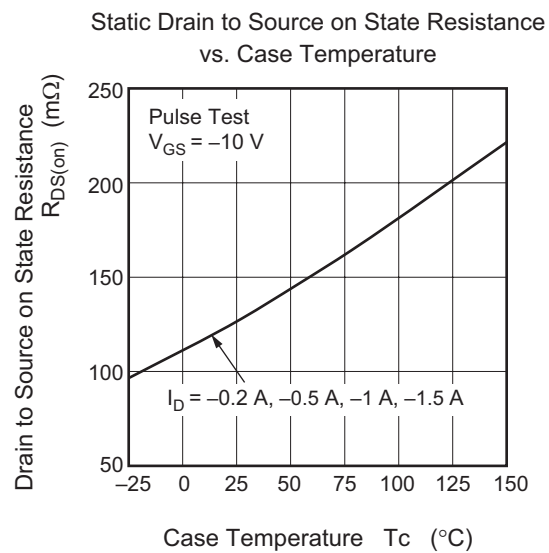
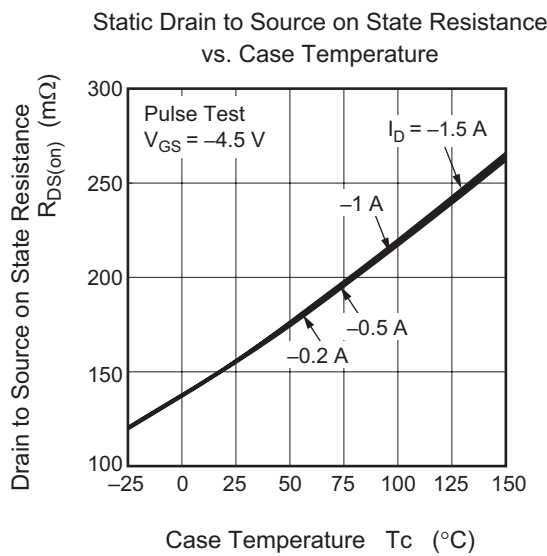
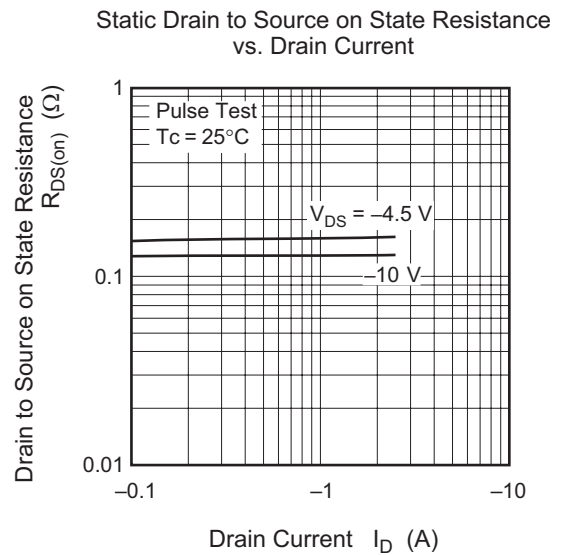
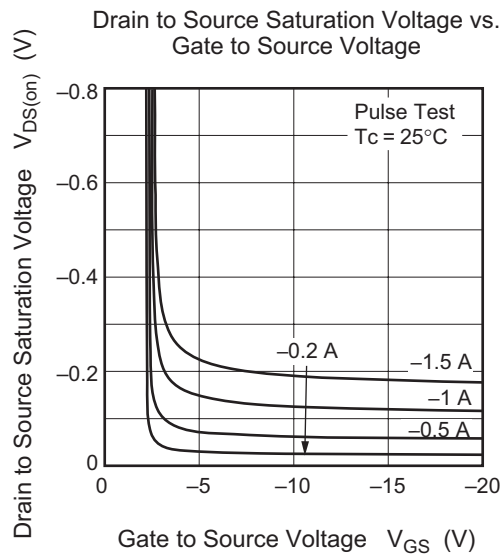
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	-60	—	—	V	$I_D = -10 \text{ mA}$ , $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	+10	—	—	V	$I_G = +100 \text{ } \mu\text{A}$ , $V_{DS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	-20	—	—	V	$I_G = -100 \text{ } \mu\text{A}$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	+10	$\mu\text{A}$	$V_{GS} = +8 \text{ V}$ , $V_{DS} = 0$
Gate to source leak current	$I_{GSS}$	—	—	-10	$\mu\text{A}$	$V_{GS} = -16 \text{ V}$ , $V_{DS} = 0$
Drain to source leak current	$I_{DSS}$	—	—	-1	$\mu\text{A}$	$V_{DS} = -60 \text{ V}$ , $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	-1.0	—	-2.0	V	$V_{DS} = -10 \text{ V}$ , $I_D = -1 \text{ mA}$
Drain to source on state resistance	$R_{DS(on)}$	—	124	155	$\text{m}\Omega$	$I_D = -1.4 \text{ A}$ , $V_{GS} = -10 \text{ V}$ <sup>Note3</sup>
	$R_{DS(on)}$	—	150	210	$\text{m}\Omega$	$I_D = -1.4 \text{ A}$ , $V_{GS} = -4.5 \text{ V}$ <sup>Note3</sup>
Forward transfer admittance	$ y_{fs} $	2.5	4.1	—	S	$I_D = -1.4 \text{ A}$ , $V_{DS} = -10 \text{ V}$ <sup>Note3</sup>
Input capacitance	$C_{iss}$	—	590	—	pF	$V_{DS} = -10 \text{ V}$ , $V_{GS} = 0$ , $f = 1 \text{ MHz}$
Output capacitance	$C_{oss}$	—	75	—	pF	
Reverse transfer capacitance	$C_{rss}$	—	36	—	pF	
Turn - on delay time	$t_{d(on)}$	—	20	—	ns	$I_D = -1 \text{ A}$ , $V_{GS} = -10 \text{ V}$ , $R_L = 10 \text{ } \Omega$ , $R_g = 4.7 \text{ } \Omega$
Rise time	$t_r$	—	41	—	ns	
Turn - off delay time	$t_{d(off)}$	—	43	—	ns	
Fall time	$t_f$	—	78	—	ns	
Total gate charge	$Q_g$	—	9.6	—	nC	$V_{DD} = -10 \text{ V}$ , $V_{GS} = -10 \text{ V}$ , $I_D = -2.8 \text{ A}$
Gate to source charge	$Q_{gs}$	—	1.3	—	nC	
Gate to drain charge	$Q_{gd}$	—	1.5	—	nC	
Body - drain diode forward voltage	$V_{DF}$	—	-0.8	—	V	$I_F = -1.5 \text{ A}$ , $V_{GS} = 0$ <sup>Note3</sup>

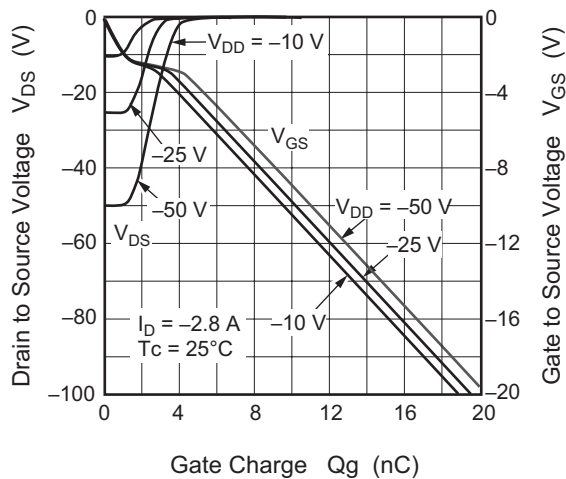
Notes: 3. Pulse test

## Main Characteristics

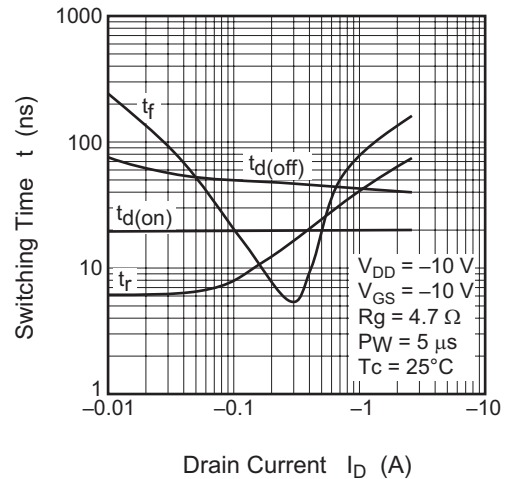




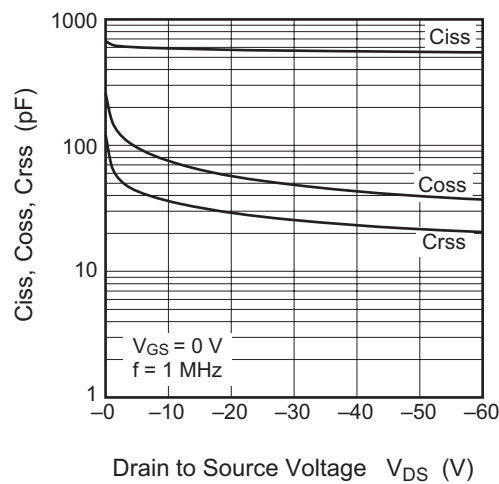
Dynamic Input Characteristics



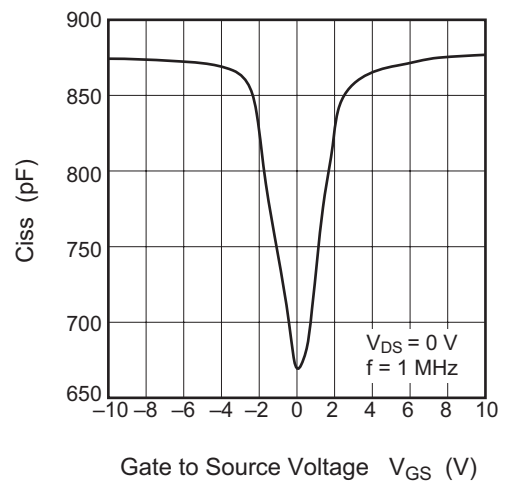
Switching Characteristics



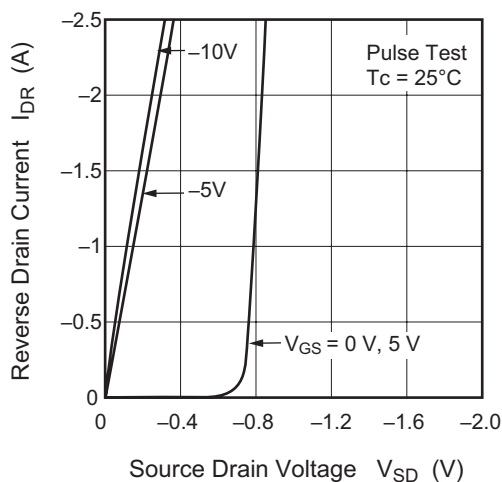
Typical Capacitance vs. Drain to Source Voltage



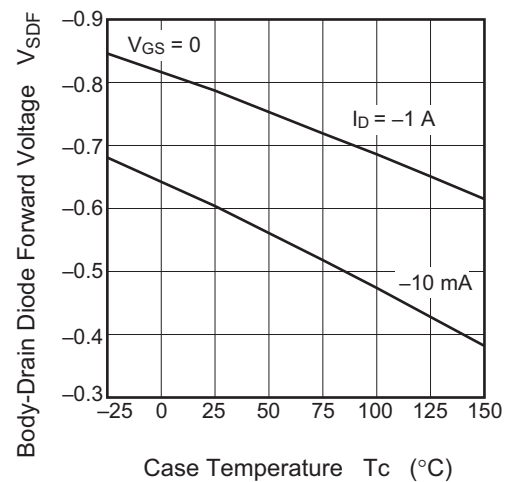
Input Capacitance vs. Gate to Source Voltage



Reverse Drain Current vs. Source to Drain Voltage



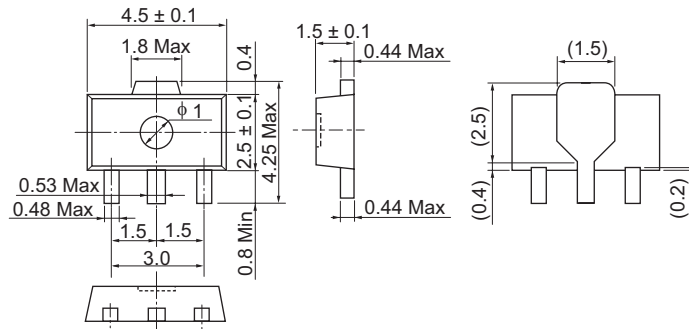
Body-Drain Diode Forward Voltage vs. Case Temperature



## Package Dimensions

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
UPAK	SC-62	PLZZ0004CA-A	UPAK / UPAKV	0.050g

Unit: mm



## Ordering Information

Part Name	Quantity	Shipping Container
RQJ0601DGDQSTL-E	1000 pcs.	$\phi$ 178 reel, 12 mm Emboss taping

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